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SPC-F005.DWG

## REVISIONS

DOC. NO. SPC-F005 \* Effective: 7/8/02 \* DCP No: 1398

DCP #	REV	DESCRIPTION	DRAWN	DATE	CHECKD	DATE	APPRVD	DATE
1885	A	RELEASED	BYF	02/08/06	HO	2/6/06	JWM	2/6/06

**Description:** Plastic, PNP, TO-220 power transistor General purpose amplifier and switching applications



### Features:

- Collector-Emitter Saturation Voltage  $I_C=1A$ ,  $I_B=0.2A$ ,  $V_{CE}=0.7V$  (Max)
- D.C. Current Gain  $I_C=.2A$ ,  $V_{CE}=4V$   $h_{FE}=40$  (Min)

### Absolute Maximum Ratings:

- Collector-Base Voltage,  $V_{CBO} = 115V$
- Collector-Emitter Voltage,  $V_{CEO} = 100V$
- Emitter-Base Voltage,  $V_{EBO} = 5V$
- Continuous Collector Current,  $I_C = 2A$
- Base Current,  $= I_B$
- Total Device Dissipation ( $T_C = +25^\circ C$ ),  $P_D = 30W$   
Derate above  $25^\circ C = 0.24mW/^\circ C$
- Operating Junction Temperature Range,  $T_J = -65^\circ C$  to  $+150^\circ C$
- Storage Temperature Range,  $T_{stg} = -65^\circ C$  to  $+150^\circ C$

**Electrical Characteristics:** ( $T_C = +25^\circ C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Max	Unit
<b>OFF Characteristics</b>					
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 30mA$ , $I_B = 0$ (Note 1)	100	—	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 1mA$ , $I_E = 0$	115	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1mA$ , $I_C = 0$	5	—	V
Collector Cut-Off Current	$I_{CES}$	$V_{CE} = 100V$ , $V_{BE} = 0$	—	0.2	mA
	$I_{CEO}$	$V_{CB} = 60V$ , $I_B = 0$	—	0.3	mA
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB} = 5V$ , $I_C = 0$	—	1	mA

### ON Characteristics (Note 1)

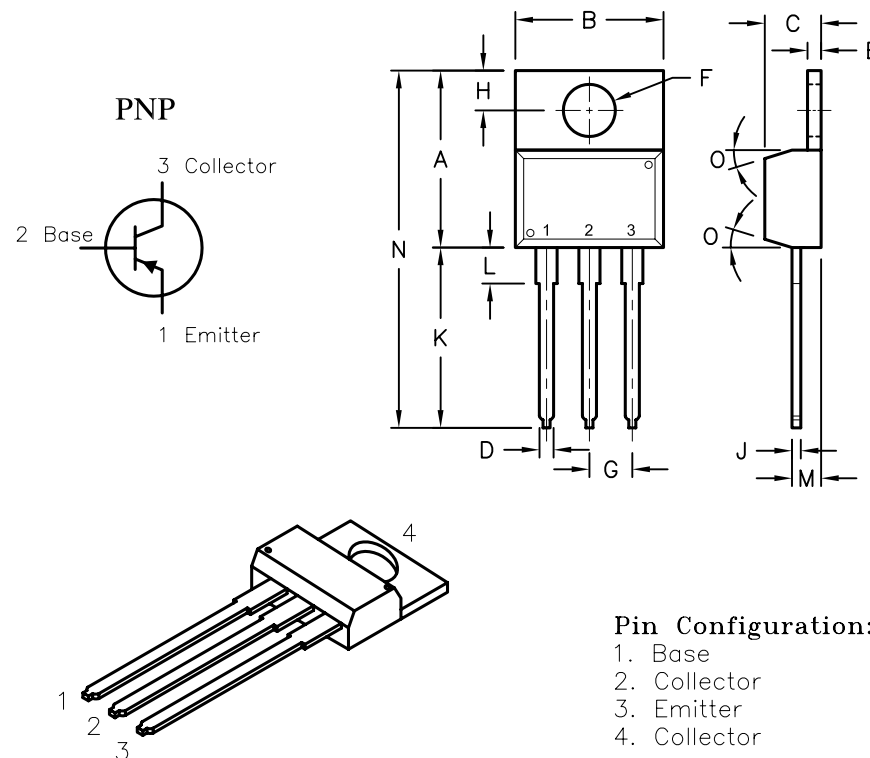
DC Current Gain	$h_{FE}$	$V_{CE} = 4V$ , $I_C = 0.2A$	40	—	—
		$V_{CE} = 4V$ , $I_C = 1A$	15	—	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1A$ , $I_B = 0.2A$	—	0.7	V
Base-Emitter Saturation Voltage	$V_{BE(on)}$	$I_C = 1A$ , $V_{CE} = 4V$	—	1.3	V

### Small-Signal Characteristics

Current Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V$ , $I_C = 0.2A$ , $f = 1MHz$	3	—	MHz
Small-Signal Current Gain	$h_{fe}$	$V_{CE} = 10V$ , $I_C = 0.2A$ , $f = 1kHz$	20	—	—

Note 1. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .

Dimensions	A	B	C	D	E	F	G	H	J	K	L	M	N	O
Min.	14.42	9.63	3.56	—	1.15	3.75	2.29	2.54	—	12.70	2.80	2.03	—	7*
Max.	16.51	10.67	4.83	0.90	1.40	3.88	2.79	3.43	0.56	14.73	4.07	2.92	31.24	



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2/6/06

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DRAWING TITLE:

General Purpose Power Transistor, Plastic, TO-220, PNP

SIZE

A

DWG. NO.

BD240C

ELECTRONIC FILE

02H2178.DWG

REV

A

SCALE: NTS

U.O.M.: MILLIMETERS

SHEET: 1 OF 1